

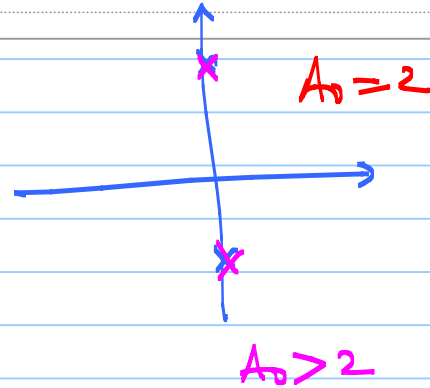
ECE 518- Lecture 19

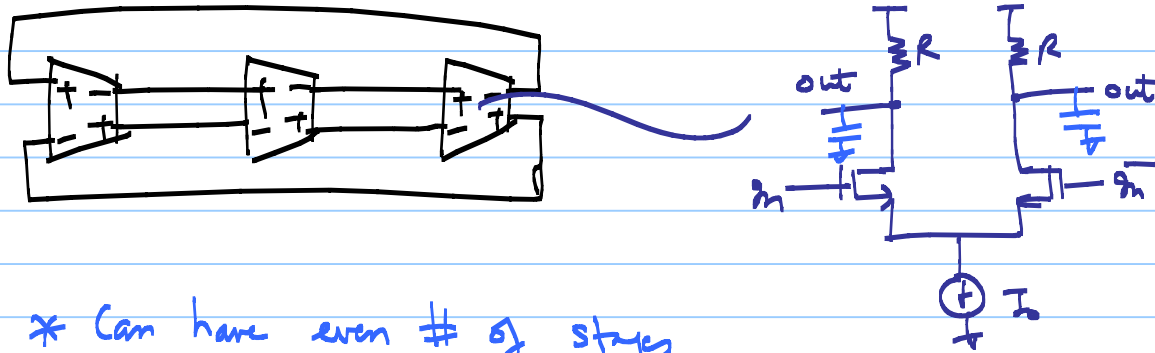
Note Title

4/2/2013

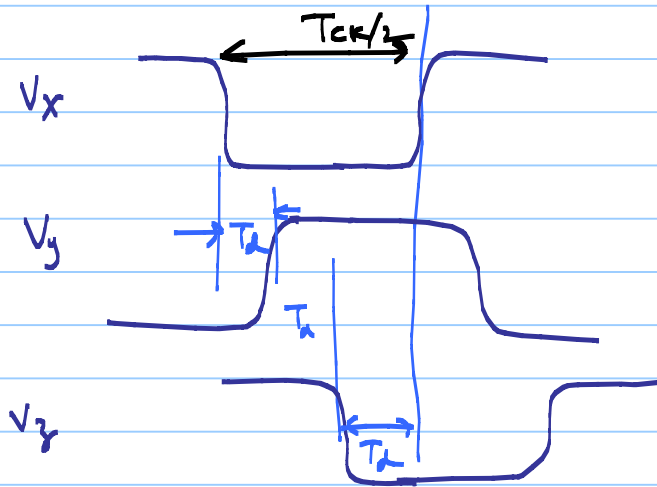
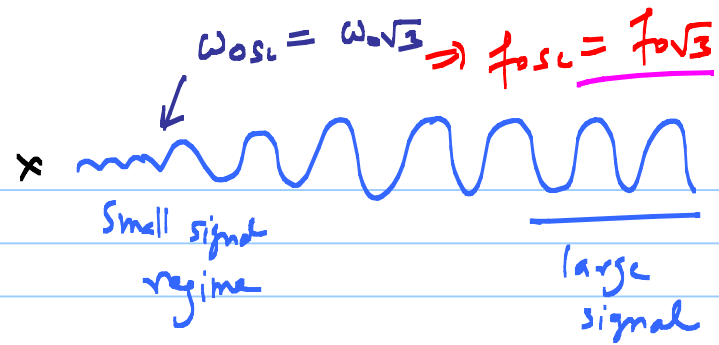
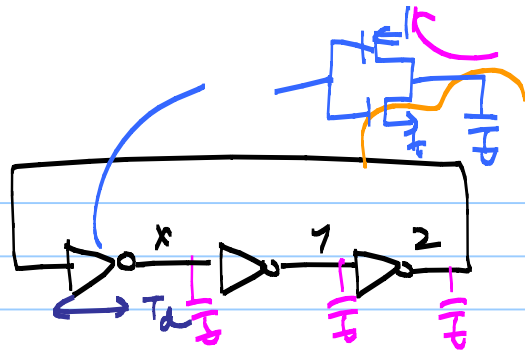
for 3-stage
oscillator

$$\omega_{osc} = \frac{A_0 \omega_0 \sqrt{3}}{2}$$





* Can have even # of stages
with differential design



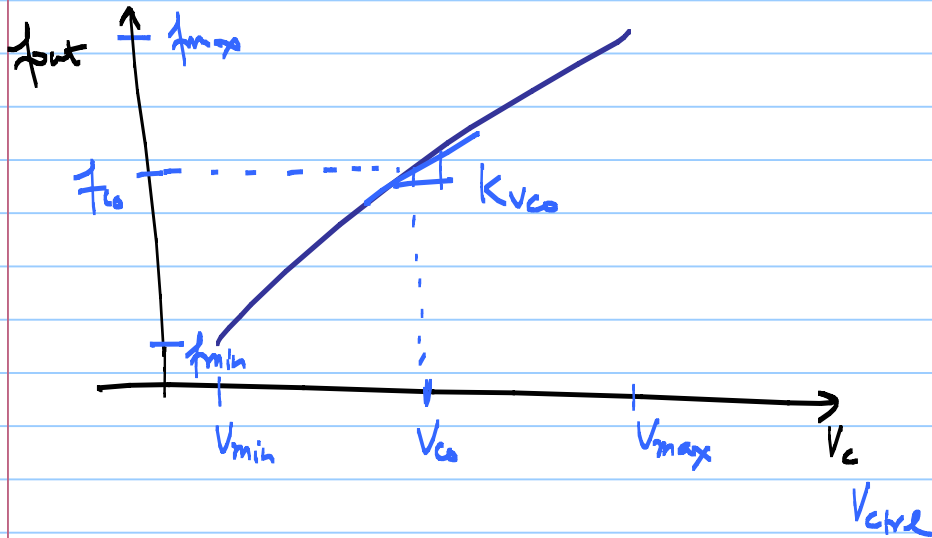
$$\frac{T_{ck}}{2} = 3T_d$$

$$\Rightarrow T_{ck} = 6T_d$$

$$\Rightarrow f_{osc} = \frac{1}{6T_d} < f_0 \sqrt{3}$$

$$\omega_0 = \frac{1}{RC}$$

VCOs

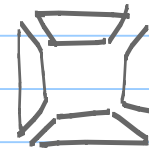


$$f_{out} = f_0 + 2\pi K_{VCO} \cdot v_c(t)$$

incremental phase domain

$$\phi_{out} = 2\pi K_{VCO} \int_{-\infty}^t v_c(t) dt$$

ASIDE
XTAL
BAW
MEMS



"SiTime"

"PVT"

Laplace
domain :

$$\phi_{out}(s) = \frac{2\pi K V_G}{s} \cdot V_c(s)$$

Performance Metrics :

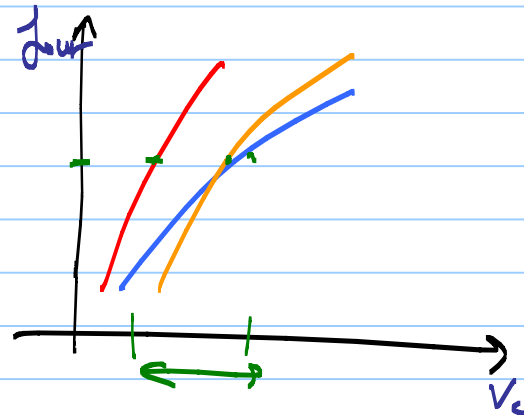
* KV_G

* Tuning range :

* 50% frequency variation
across PVT corners

* Need a wide-enough tuning
range to cover PVT variation

→ ASIC's need 5X tuning range



Spec're

* UltraSim

* FactSpice

* UltraSpice

* Tuning Linearity:

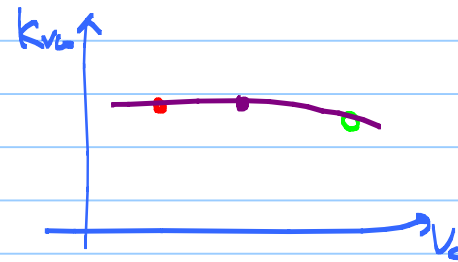
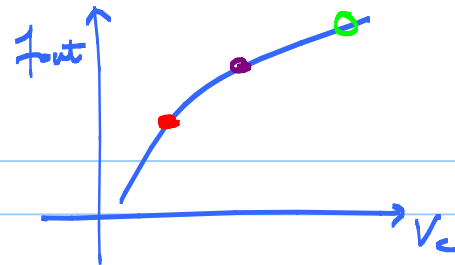
↳ K_{VCO} depends upon f_{out}

↳ Affects loop dynamics

↳ BW & PM

↳ ring $V_{CO} \rightarrow 2-3\times$ variation

↳ can "linearize" V_{CO}



* Power

→ tradeoff noise & power

* PSRR

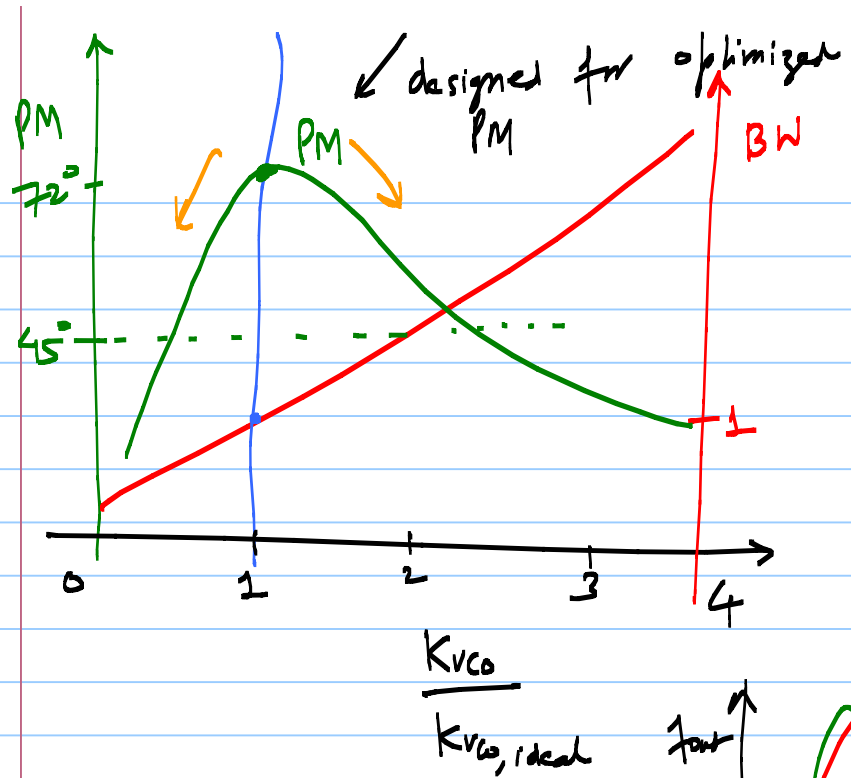
⇒ power supply noise should not limit the filter performance

Tuning linearity



$$K_{VCO} = f(f_{out})$$

↳ behavior depends upon the operating frequency



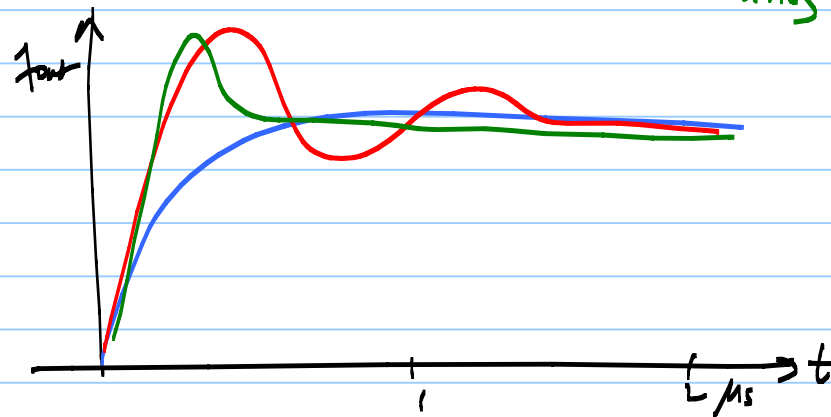
Small signal loop-gain

$$L(s) = \frac{K_{vco} T_0}{N} \frac{(s + \frac{1}{R_1 C_1})}{s^2 C_2 (s + \frac{1}{R_1 || C_2})}$$

$\hookrightarrow \omega_{u,loop}$ varies with K_{vco}

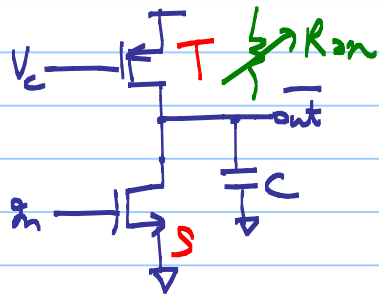
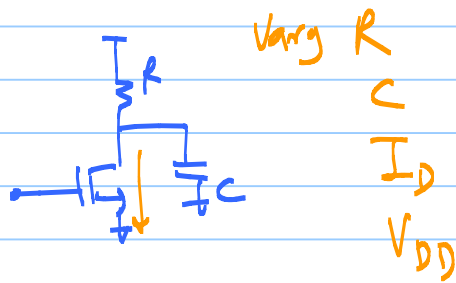
$\hookrightarrow \omega_{3dB}, \zeta$

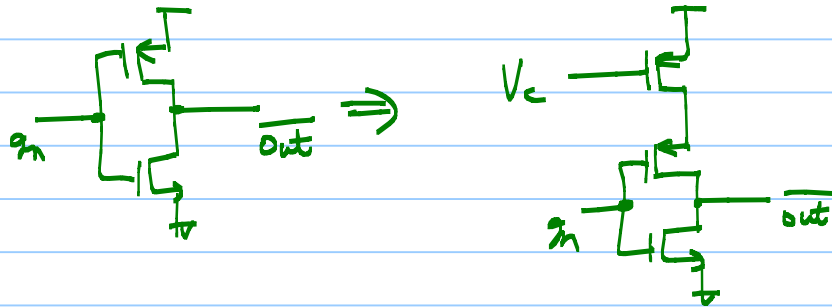
$\hookrightarrow PM$ also varies



VCO Tuning

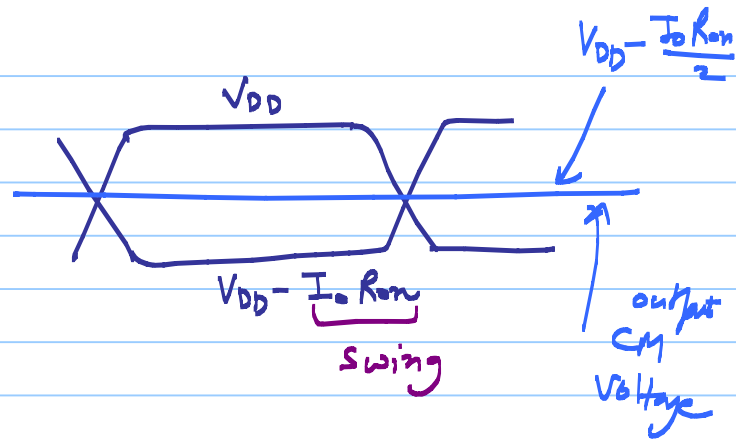
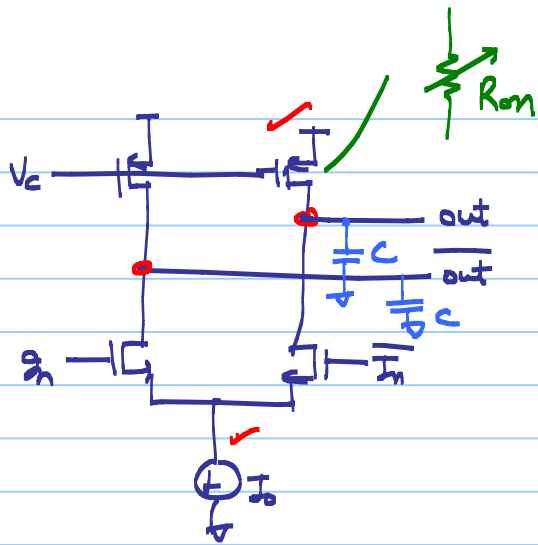
↳ Need a knob to control the oscillation frequency.





Need:

- * Wide tuning range
- * good linearity
- * No phase noise generation



$$\tau = R_{on} C = \frac{C}{K \mu_n \frac{W}{L} (V_{DD} - V_c - |V_{THP}|)}$$

R_{on}^{-1}
assuming
deep Triode
 $V_{DS} \ll V_{DS,sat}$

$$f_{out} \propto \frac{1}{\tau} \propto \frac{K \mu_n \frac{W}{L} (V_{DD} - V_c - |V_{THP}|)}{C}$$

* I_{out} varies with V_c

↳ Valid only when the load Transistors are in Triode

$$V_{DS} = I_0 R_{on} = \frac{I_0}{K_p \frac{W}{L} (V_{DD} - V_c - V_{THP})} \ll \overbrace{(V_{DD} - V_c)}^{V_{SG}} - V_{THP}$$

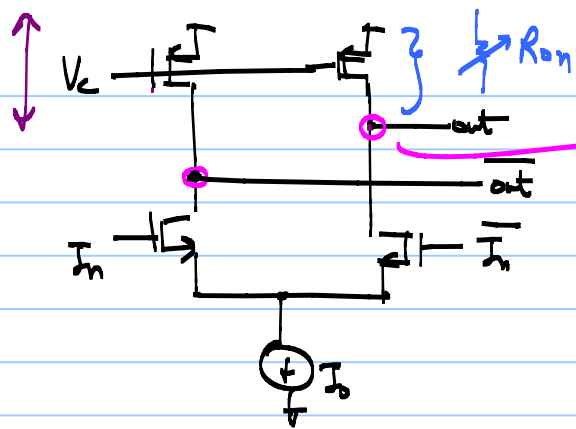
* If the above condition is not satisfied

↳ load transistors saturate

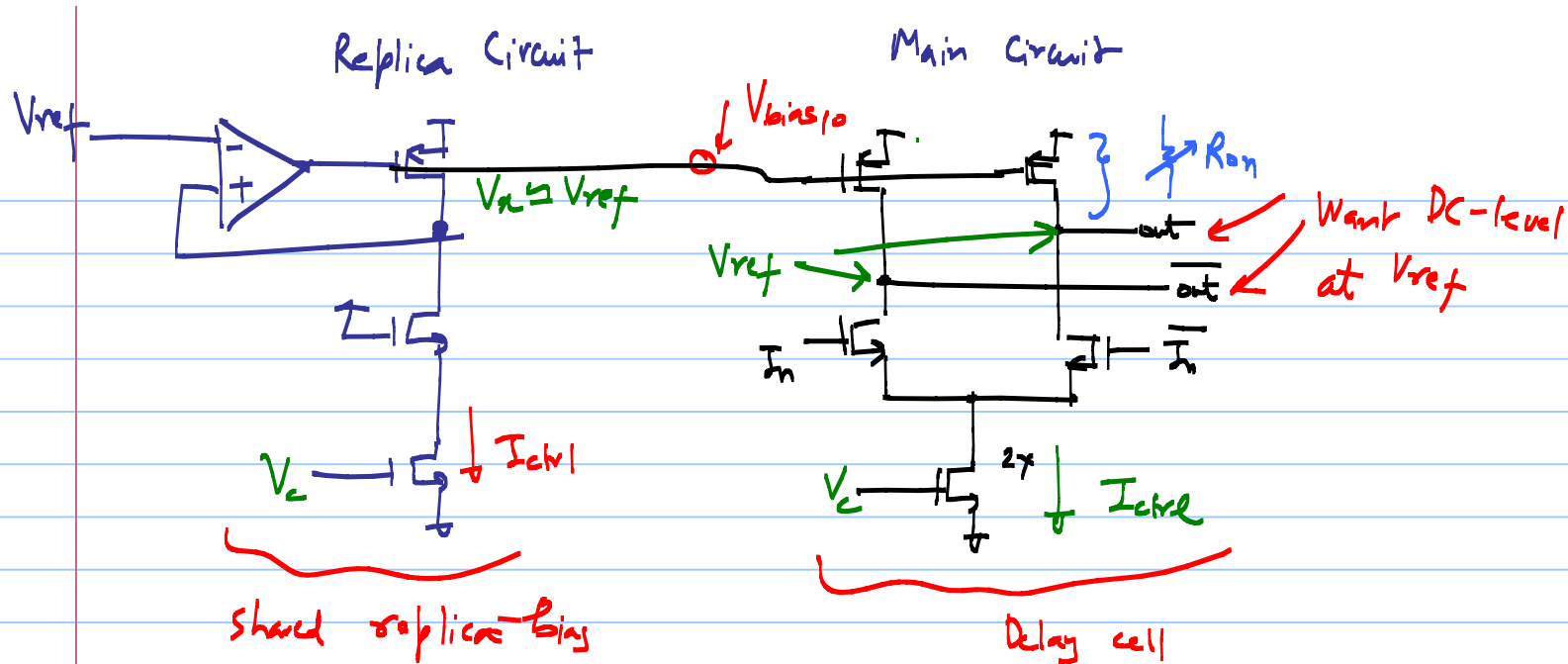
↳ V_{GS} characteristics saturates

↳ output CM voltage is undefined

* Output swing is frequency dependant



fix the output CM-level

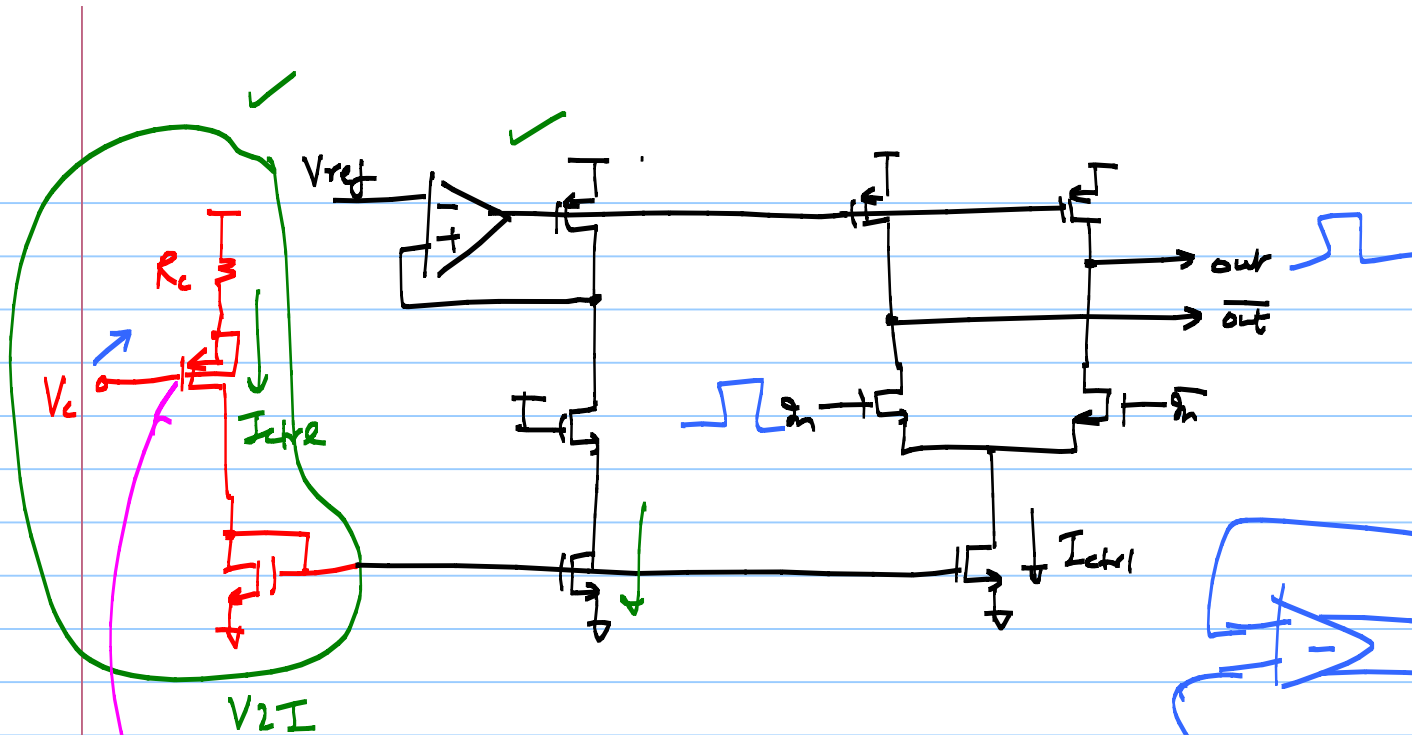


Replica bias forces

$$R_{on} = \frac{(V_{DD} - V_{ref})}{I_{ctrl}}$$

$$f_{out} \propto \frac{1}{R_{on}C} \propto \frac{I_{ctrl}}{(V_{DD} - V_{ref})C}$$

$$I_{ctrl} = f(V_c) \leftarrow \text{non-linearity of the NMOS}$$



$$f_{out} \propto \frac{-V_{ctrl}}{R_c (V_{DD} - V_{ref}) C}$$

$$g_m \gg 1/R_c$$

